

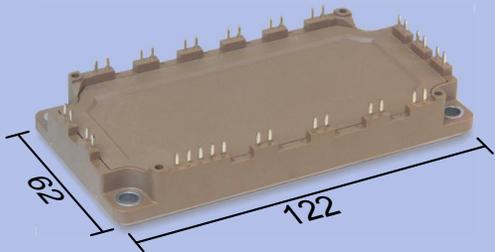
# Fuji Hybrid Modules (Si-IGBT and SiC-FWD)

## Higher efficiency with SiC free wheeling diodes

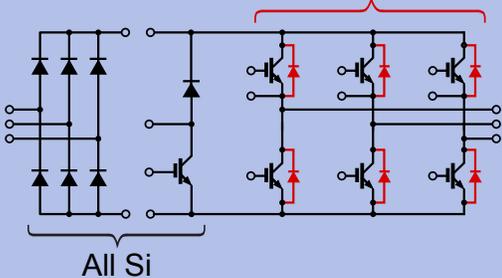
- Lower Turn-on and reverse recovery losses
- Low leakage current at higher temperatures
- Suitable for high switching frequency application

### PIM

(Power Integrated Module)



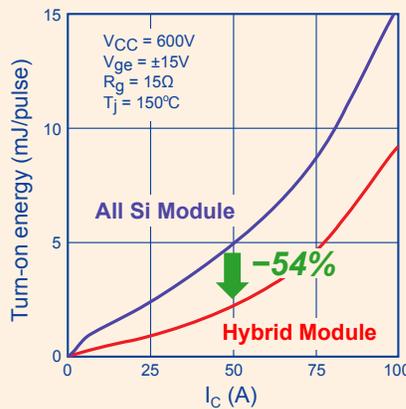
Si IGBT +  
SiC Schottky diode



$I_c$	600V	1200V
35A		●
50A	●	●
75A	●	
100A	●	

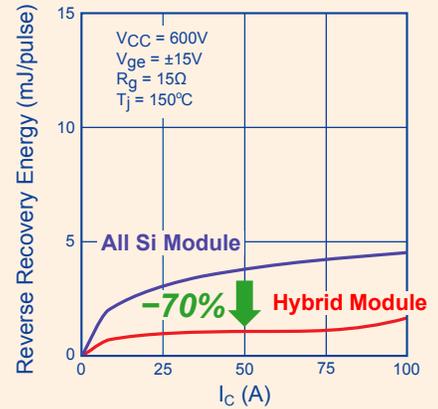
### IGBT turn-on switching loss

$E_{on}$



### Diode turn-off switching loss

$E_{rr}$



### Conditions:

$V_{dc} = 600V$ ,  $I_o = 35A_{rms}$ ,  $f_o = 50Hz$ ,  $pf = 0.9$ ,  
 $V_{ge} = \pm 15V$ ,  $R_g = 15\Omega$ ,  $T_j = 150^\circ C$

